Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application. In the claim listing, new claims 33-36 are added and no claims are deleted.

1. (Currently Amended) A method for manufacturing an organic electroluminescent display, comprising ~~the steps of~~:

forming a substantially transparent substrate;

forming a plurality of first display electrodes arranged in parallel on said substrate;

forming a non-photosensitive insulating layer ~~on~~ over said substrate ~~with first display electrodes disposed thereon~~;

applying a cross-linking process to said non-photosensitive insulating layer;

forming a photosensitive insulating layer on said non-photosensitive insulating layer;

performing a photolithography process on said photosensitive insulating layer;

developing said photosensitive insulating layer and etching said non-photosensitive insulating layer so as to form ~~a plurality of~~ a pattern of photosensitive insulating layer and ~~the~~ non-photosensitive insulating layer having a shape with ~~its~~ a longitudinal axis substantially perpendicular to ~~the that~~ a longitudinal axis of the first display electrodes, and the first display electrodes being exposed partly;

forming an organic electroluminescent material on the exposed first display electrodes; and

forming a plurality of second display electrodes on the organic electroluminescent material.

2. (Original) The method according to claim 1, wherein the non-photosensitive insulating layer is made of a thermal type polyimide.

3. (Original) The method according to claim 1, wherein the thickness of the non-photosensitive insulating layer is in a range of 0.5-2μm.

4. (Currently Amended) The method according to claim 1, wherein ~~the step of forming~~ applying a cross-linking process to the non-photosensitive insulating layer ~~further~~ comprises performing a ~~baking~~ baking process ~~for providing partial cross-linking to the non-photosensitive insulating layer~~.

5. (Currently Amended) The method according to claim 4, wherein the temperature ~~for baking~~ of the baking process ~~said non-photosensitive insulating layer~~ is in a range of about 120-180 Celsius degrees.

6. (Currently Amended) The method according to claim 4, wherein the duration time ~~for baking~~ of the baking process ~~said non-photosensitive insulating layer~~ is in a range of about 20-60 minutes.

7. (Currently Amended) The method according to claim 1, wherein the thickness of the photosensitive insulating layer is in a range of about 3-5μm.

8. (Currently Amended) The method according to claim 1, wherein the exposure to

the photosensitive insulating layer during the photolithography process is in a range of about 30-80mJ/cm^2.

9. (Currently Amended) The method according to claim 1, wherein ~~the step of~~ developing the photosensitive insulating layer and etching the non-photosensitive insulating layer is proceeded through a developers solution.

10. (Currently Amended) The method according to claim 9, wherein the developer solution is TMAH 2.38%.

11. (Currently Amended) The method according to claim 9, wherein the duration time for developing the photosensitive insulating layer and etching the non-photosensitive insulating layer is in a range of about 50-100 seconds.

12. (Currently Amended) The method according to claim 1, wherein the photosensitive insulating layer is developed into a reversed trapezoid shape.

13. (Currently Amended) The method according to claim 12, wherein a long ~~side~~ base of the reversed trapezoid shape of the photosensitive insulating layer is ~~not shorter~~ longer than or equal to ~~that of the reversed trapezoid~~ a bottom edge of the shape of the etched non-photosensitive insulating layer.

14. (Currently Amended) The method according to claim 1, wherein the non-

photosensitive insulating layer is ~~etching~~ etched into a ~~reversed~~ trapezoid shape.

15. (Currently Amended) The method according to claim 14, wherein ~~long side~~ a top edge of the ~~trapezoid~~ shape of the developed photosensitive insulating layer is ~~not shorter~~ longer than or equal to ~~that~~ a long base of the ~~reversed~~ trapezoid shape of the non-photosensitive insulating layer.

16. (Currently Amended) The method according to claim 1, wherein ~~the step of~~ developing the photosensitive insulating layer and etching the non-photosensitive insulating layer further comprises performing a ~~final cure~~ curing process.

17. (Currently Amended) The method according to claim 16, wherein the temperature ~~for proceeding~~ of the ~~final cure~~ curing process is in a range of about 200-350 Celsius degrees.

18. (Currently Amended) The method according to claim 16, wherein the duration time ~~for proceeding~~ of the ~~final cure~~ curing process is in a range of about 30-120 minutes.

19. (Currently Amended) A method for manufacturing an organic electroluminescent display, comprising ~~the steps of~~:

forming a substantially transparent substrate;

forming a plurality of first display electrodes arranged in parallel on said substrate;

forming a non-photosensitive insulating layer ~~on~~ over said substrate ~~with first display electrodes disposed thereon~~;

~~pre-baking and baking~~ applying a baking process to said non-photosensitive insulating layer;

forming a photosensitive insulating layer on said non-photosensitive insulating layer, and pre-baking ~~thereto~~ said photosensitive insulating layer;

performing a photolithography process on said photosensitive insulating layer so as to define a shape having a longitudinal axis perpendicular to ~~the that~~ a longitudinal axis of the first display electrodes, and performing a post-exposure baking process ~~thereto~~ on said photosensitive insulating layer;

dipping an aggregate composed of said substrate with said first display electrodes, said non-photosensitive insulating layer and said photosensitive insulating layer disposed thereon into a ~~developers~~ developer solution, whereby said photosensitive insulating layer is partially removed through development and said non-photosensitive insulating layer is partially removed by etching, and thereby said first display electrodes are exposed partially;

~~finally~~ curing said aggregate;

forming an organic electroluminescent material on the exposed first display electrodes; and

forming a plurality of second display electrodes on the organic electroluminescent material.

20. (Original) The method according to claim 19, wherein the non-photosensitive insulating layer is made of a thermal type polyimide.

21. (Currently Amended) The method according to claim 19, wherein the temperature

~~for pre-baking~~ of baking said non-photosensitive insulating layer is in a range of about 50-120 Celsius degrees.

22. (Currently Amended) The method according to claim 19, wherein the temperature ~~for~~ of post-exposure baking said photosensitive insulating layer is in a range of about 90-150 Celsius degrees.

23. (Currently Amended) The method according to claim 19, wherein the duration time ~~for~~ of post-exposure baking said photosensitive insulating layer is in a range of about 30-120 seconds.

24. (Currently Amended) The method according to claim 19, wherein the photosensitive insulating layer is developed into a reversed trapezoid shape.

25. (Currently Amended) The method according to claim 24, wherein a long ~~side~~ base of the reversed trapezoid shape of the photosensitive insulating layer is ~~not shorter~~ longer than ~~that~~ or equal to a bottom edge of the shape ~~reversed trapezoid shape~~ of the etched non-photosensitive insulating layer.

26. (Currently Amended) The method according to claim 19, wherein the non-photosensitive insulating layer is etched into a ~~reversed~~ trapezoid shape.

27. (Currently Amended) The method according to claim 26, wherein ~~long side~~ a top

edge of the ~~trapezoid~~ shape of the developed photosensitive insulating layer is ~~not shorter~~ longer than ~~that~~ or equal to a long base of the ~~reversed~~ trapezoid shape of the non-photosensitive insulating layer.

28. (Currently Amended) A method for manufacturing an organic electroluminescent display, comprising ~~the steps of~~:

forming a substantially transparent substrate;

forming a plurality of first display electrodes arranged in parallel on said substrate;

forming a first photosensitive insulating layer ~~on~~ over said substrate ~~with first display electrodes disposed thereon~~;

forming a second photosensitive insulating layer on said first photosensitive insulating layer;

performing a photolithography process on said first and second photosensitive insulating layers;

developing said first and second photosensitive insulating layers simultaneously so as to form a ~~plurality~~ pattern of first and second photosensitive insulating layers having a shape with ~~its~~ a longitudinal axis substantially perpendicular to ~~the that~~ a longitudinal axis of the first display electrodes, and the first display electrodes being exposed partly;

forming an organic electroluminescent material on the exposed first display electrodes; and

forming a plurality of second display electrodes on the organic electroluminescent material,

wherein the photosensitivity of the first photosensitive insulating layer is different from

that of the second photosensitive insulating layer.

29. (Currently Amended) The method according to claim 28, wherein ~~the step of~~ developing said first and second photosensitive insulating layers is proceeded through ~~developers~~ a developer solution.

30. (Original) The method according to claim 28, wherein the photosensitivity of said first photosensitive insulating layer is greater than that of said second photosensitive insulating layer.

31. (Currently Amended) A method for manufacturing an organic electroluminescent display, comprising ~~the steps of~~:

forming a substantially transparent substrate;

forming a plurality of first display electrodes arranged in parallel on said substrate;

forming a first photosensitive insulating layer ~~on~~ over said substrate ~~with first display electrodes disposed thereon~~;

forming a second photosensitive insulating layer on said first photosensitive insulating layer;

performing a photolithography process on said first and second photosensitive insulating layers so as to define a shape having a longitudinal axis perpendicular to ~~that~~ a longitudinal axis of the first display electrodes;

dipping an aggregate composed of said substrate with said first display electrodes, said first photosensitive insulating layer and said second photosensitive insulating layer disposed

thereon into a ~~developers~~ developer solution, whereby said first and second photosensitive insulating layers are partially removed through development, and thereby said first display electrodes are exposed partially;

forming an organic electroluminescent material on the exposed first display electrodes; and

forming a plurality of second display electrodes on the organic electroluminescent material.

32. (Original) The method according to claim 31, wherein the photosensitivity of said first photosensitive insulating layer is greater than that of said second photosensitive insulating layer.

33. (New) A method for manufacturing an electroluminescent display, comprising:

forming a first electrode on a substrate;

forming a non-photosensitive insulating layer to cover said first electrode;

forming a photosensitive insulating layer on said non-photosensitive insulating layer;

applying a photolithography process to said photosensitive insulating layer;

developing said photosensitive insulating layer and etching said non-photosensitive insulating layer using one same active solution to form a pattern of insulating material that partially exposes the first electrode;

forming an electroluminescent material on the exposed first electrode; and

forming a second electrode on the electroluminescent material.

34. (New) The method according to claim 33, further comprising applying a cross-linking process to said non-photosensitive insulating layer.

35. (New) A method for manufacturing an electroluminescent display, comprising:

forming a first electrode on a substrate;

forming a non-photosensitive insulating layer to cover said first electrode;

applying a cross-linking process to said non-photosensitive insulating layer;

forming a photosensitive insulating layer on said non-photosensitive insulating layer;

applying a photolithography process to said photosensitive insulating layer;

developing said photosensitive insulating layer and etching said non-photosensitive insulating layer to form a pattern of insulating material that partially exposes the first electrode;

forming an electroluminescent material on the exposed first electrode; and

forming a second electrode on the electroluminescent material.

36. (New) A method for manufacturing an electroluminescent display, comprising:

forming a first electrode on a substrate;

forming a first photosensitive insulating layer to cover said first electrode over said substrate;

forming a second photosensitive insulating layer on said first photosensitive insulating layer, wherein the photosensitivity of the first photosensitive insulating layer is different from that of the second photosensitive insulating layer;

applying a photolithography process to said first and second photosensitive insulating layers;

developing said first and second photosensitive insulating layers to form a pattern of insulating material that partially exposes the first electrode;

forming an electroluminescent material on the exposed first electrode; and

forming a second electrode on the electroluminescent material.